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Thermal acoustic excitations with atomic-scale wavelengths in amorphous silicon

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Abstract

The vibrational properties of glasses remain a topic of intense interest due to several unresolved puzzles, including the origin of the Boson peak and the mechanisms of thermal transport. Inelastic scattering measurements have revealed that amorphous solids support collective acoustic excitations with low THz frequencies despite the atomic disorder, but these frequencies are well below most of the thermal vibrational spectrum. Here, we report the observation of acoustic excitations with frequencies up to 10 THz in amorphous silicon. The excitations have atomic-scale wavelengths as short as 6 Å and exist well into the thermal vibrational frequencies. Simulations indicate that these high frequency waves are supported due to the high group velocity and monatomic composition of a-Si, suggesting that other glasses with these characteristics may also exhibit such excitations. Our findings demonstrate that a substantial portion of thermal vibrational modes in amorphous materials can still be described as a phonon gas despite the lack of atomic order.

I. INTRODUCTION

Amorphous materials possess a number of peculiar vibrational properties compared to those of their crystalline counterparts^{1–7}. For vibrations of frequency less than a few THz, the wavelengths are sufficiently long that the vibrational properties would be expected to be unaffected by the atomic disorder⁸. However, the observed density of states and heat capacity of glasses differ from the Debye predictions at low temperatures below 10 K^{1–7}. Various explanations have been proposed for these observations, including the soft potential model^{9,10}, elastic heterogeneities¹¹, and lower mass density of amorphous solids compared to their crystalline counterparts^{6,7}.

The introduction of high brilliance inelastic X-ray scattering (IXS) experiments has enabled acoustic excitations to be resolved by wave vector and energy outside of the dynamic range accessible by neutron scattering^{12–16}. The measurements have shown that many glasses^{17–22} and liquids^{23–26} support isotropic acoustic excitations with frequencies up to ~ 1 THz despite the atomic disorder. Further, the observed inelastic peaks exhibit a broadening, $\Gamma(q)$, that increases with wave vector q following a power law^{17–22,25–30}. The acoustic excitation ceases to be well-defined when the broadening is on the order of the frequency of the excitation, typically around a few THz. These general trends have been reported in a variety of glasses including polymers^{18,28,30}, metallic glasses²¹, monatomic glasses such as selenium²⁰, and others^{17,19,22,27,29}.

Numerical methods such as molecular dynamics simulations are often utilized to gain microscopic understanding of vibrational properties in amorphous materials and to guide experimental measurements. Amorphous silicon has been used for decades as a representative material to understand the vibrational properties of amorphous materials due to its monoatomic composition and widely used available potentials such as Stillinger-Weber^{31,32} and Tersoff^{33,34}. Prior computational works based on normal mode decomposition have concluded that propagating acoustic waves exist up to ~ 2 THz to 3 THz^{35–40} and that non-propagating vibrations dominate the thermal conductivity^{35,37–40}. On the other hand, recent calculations predicted that acoustic-like vibrations are present well into the thermal frequencies^{41,42}. The conflict between these reports remains unresolved due to the lack of inelastic scattering measurements that provide direct information on the acoustic excitations supported in a-Si.

Here, we report the observation of acoustic excitations with atomic-scale wavelengths as small as 6 Å, corresponding to frequencies up to 10 THz using IXS. Molecular dynamics simulations show that these high frequency acoustic waves are supported due to the high group velocity and monatomic composition of a-Si, and that these results hold for a variety of atomic configurations that match the observed radial distribution function. Such excitations extending in the thermal frequencies might also be found in other elastically stiff monatomic glasses such as tetrahedral amorphous carbon. Our findings indicate that the phonon gas model describes thermal atomic vibrations accurately in amorphous Si despite the lack of atomic order.

II. SAMPLE PREPARATION

We prepared two samples (A1 and A2) by depositing amorphous Si onto sapphire substrates by plasma enhanced chemical vapor deposition (PECVD) at separate times with silane gas diluted (5%) in argon gas at a deposition table temperature of 473 K. To make a sample suitable for the X-ray beam with absorption length of 2 mm, a-Si thin films (3 μ m thick) were powderized in the glovebox under either nitrogen or argon and placed in quartz capillary tubes with 10 μ m wall thickness. The structural characterization of sample A1 is shown in Fig. 1. The radial distribution function (RDF) of this sample was measured by neutron scattering at Nanoscale-Ordered Materials Diffractometer (NOMAD), Spallation Neutron Source (SNS) at Oak Ridge National Laboratory. The neutron total scattering structure function was produced by normalizing the sample scattering intensity to the scattering intensity from a solid vanadium rod and subtracting the background of an empty 2 mm quartz capillary. The radial distribution function was obtained through the Fourier transform of the total scattering function with momentum transfer between 0.1 and 31.4 Å⁻¹. The RDF and X-ray diffraction pattern show broadened features, indicating that the samples are disordered. The RDF indicates that residual hydrogen ($\sim 20 \text{ at.}\%$) is present in the sample as indicated by the negative peak at the Si-H 1.4 Å distance, but we expect little influence on our measurements considering that prior work observed no systematic change in thermal conductivity of PECVD amorphous silicon films with hydrogen content varying from 1 at. % to 20 at. $\%^{43}$.



FIG. 1. Structural characterization of a-Si powders. (a) Radial distribution function (blue circles) of the sample A1 compared to a calculation using an amorphous structure from molecular dynamics $(line)^{42}$. (b) X-ray diffraction pattern measured at 300 K. Each tick mark represents $2\theta = 2.5^{\circ}$ at x-ray energy of 21.657 keV. Broadened features in both the RDF and XRD measurements indicate an amorphous atomic structure.

III. RESULTS

A. Inelastic X-ray scattering measurements

Dynamic structure factors from both samples (A1 and A2) were independently measured using spectrometers at sector HERIX-3 and HERIX-30 with energies of 21.657 and 23.71 keV at the Advanced Photon Source (APS)^{44–47}, respectively. The measurements for the longitudinal branch at different momentum transfers at room temperature are shown in Figs. 2 (a) and (b), respectively. For both samples, distinct inelastic peaks are clearly visible at thermal frequencies up to around 10 THz, indicating the presence of collective acoustic excitations with well-defined frequencies and wave vectors. The wavelengths of these excitations are as small as 6 Å, comparable to the interatomic spacing in a-Si. A sudden increase in the broadening of the inelastic peaks is observed between 7.79 nm⁻¹ and 11.12 nm^{-1} for A1 and between 10.0 nm⁻¹ and 12.0 nm⁻¹ for A2, respectively. This visual observation indicates that collective excitations with well-defined wave vector and frequency are not supported beyond these wave vectors and frequencies.



FIG. 2. Inelastic X-ray scattering spectra of (a) sample A1 (black circles) and (b) sample A2 (blue circles) along with the fit (red lines). For both samples, sharp inelastic peaks are observed at frequencies approaching 10 THz, above which a significant increase in the broadening is seen.

To determine the center frequencies and the broadening of the collective excitations at each momentum transfer, the dynamic structure factor spectra were modeled with a function $S(q, \nu)$ consisting of a Lorentzian for the central elastic peak and a damped harmonic oscillator for the inelastic peaks:

$$S(q,\nu) = I_0(q) \frac{\Gamma_0(q)^2}{\Gamma_0(q)^2 + \nu^2} + [n(\nu) + 1]I(q) \frac{\nu \Gamma(q)^2 \Omega(q)}{[\Omega(q)^2 - \nu^2]^2 + \Gamma(q)^2 \nu^2}$$
(1)

where q is the wave vector, ν is the frequency, $I_0(q)$ and $\Gamma_0(q)$ are the intensity and width of the central peak, I(q) and $\Gamma(q)$ are the intensity and full width half maximum of the inelastic peak with the peak frequency $\Omega(q)$, and $n(\nu)$ is the Bose factor²³. The function $S(q,\nu)$ is then convoluted with the pseudo-Voigt function representing the resolution function to fit to the experimental data⁴⁴.



FIG. 3. Dispersion relation from IXS measurements (diamonds from A1 using HERIX sector 3 and filled circles from A2 using HERIX sector 30) and calculated dynamic structure factor from Moon *et al.*⁴². Vertical bars represent the FWHM of the inelastic peaks. The sound velocity from the measurements is 7850 m s⁻¹, within 4% of the predicted sound velocity of 8179 m s⁻¹.

The dispersion relations of the measured acoustic excitations are plotted in Fig. 3 along

with the calculated dynamic structure factor from Ref.⁴². The vertical bars represent the full width at half maximum of the inelastic peaks. Excellent agreement between the simulation and the IXS measurements is observed, with the sound velocities agreeing to within 4%. We attempted to include the 20 at.% hydrogen present in the sample in MD simulations using available interatomic potentials⁴⁸; however, the thermal conductivity of the structure was inconsistent with experiments⁴⁹. This discrepancy may arise because the interatomic potential was optimized for structural rather than dynamic properties. The good agreement between simulations with pure a-Si and experiments suggests that the presence of hydrogen does not affect the dispersion of the acoustic excitations. In both simulations and experiments, vibrations with frequencies less than ~ 10 THz have a well-defined frequency and wave vector. As shown in Fig. S1 in the Supplementary Material⁵⁰, the calculated dynamic structure factors of Ref.³⁸ and⁴¹ are also in good agreement with the measurements. These works also utilized Stillinger-Weber potential³¹. Comparison with other theoretical studies that focus on quantities of relevance to Allen-Feldman theory^{35,51} is difficult because such quantities are not directly measured in an IXS experiment.

Next, we performed additional temperature dependent IXS measurements on Sample A1 at 35 K and 500 K. The extracted inelastic peak frequencies and broadenings are shown in Fig. 4. We observe a slight softening with temperature for the peak frequency, $\Omega(q)$, but no temperature dependence of the broadening is seen. This observation indicates that the origin of the broadening of the inelastic peaks is structural rather than anharmonic. The temperature independence of the broadening has also been reported in other amorphous solids such as glycerol and silica^{19,27,52}.



FIG. 4. Temperature dependent IXS measurements for sample A1 (a) Inelastic peak frequency and (b) broadening at wave vectors of 7.79 (blue circles), 11.12 (red diamonds), and 14.44 nm⁻¹ (black squares) across the temperature range from 35 to 500 K. A slight softening of the peak frequencies with temperature is observed but no clear temperature dependence is found for the broadenings.

IV. DISCUSSION

A. Dynamic structure factor of various atomic configurations

We note that a-Si does not have a uniquely determined structure. Prior calculations^{53,54} have shown that paracrystalline amorphous silicon structures yield an RDF that is indistinguishable with that of experiments. We therefore generated 3 different amorphous silicon configurations (continuous random network, melt-quench, and crystal seed nucleation) that closely match with our RDF from neutron scattering. All three structures contain 4096 atoms and use the same SW potential with a time constant of 0.5 fs. The continuous random network model was provided by N. Mousseau and was generated from the modified Wooten-Winer-Weaire (WWW) algorithm⁵⁵. The description of the melt-quench method is provided in detail in Moon et al.⁴². For the crystal seed nucleation method, the crystalline silicon was first melted at 3500 K at constant volume for 50 ps while the spherical crystal seed atoms (1 at.%) are kept fixed at their positions. We then quenched the structure to 1000 K at 1000 K ps⁻¹. The entire structure was then annealed at 1000 K and 0 bar for 2.75 ns in NPT followed by quenching to room temperature at the same rate as before. The resulting structure from the crystal seed nucleation, therefore, has a crystalline region as



FIG. 5. (a) Paracrystalline amorphous silicon structure with only the crystalline region displayed. (b) Zoomed-in view of the crystallite. The red atoms denote the initial crystal seed and the black atoms represent the crystal growth from annealing. The crystallite is estimated to compose 8 at.% of the structure. The crystal order is clearly observed. (c) Radial distribution function of continuous random network (black line), melt-quench (blue line), and paracrystalline (red line) amorphous silicon structures compared to that of experimental data (green circles).

shown in Fig. 5 (a). Only the crystallite atoms are displayed in the otherwise amorphous domain.

A zoomed-in view of the crystallite is depicted in Fig. 5 (b). The red atoms denote

the initial crystal seed (1 at.%) and the black atoms represent the crystal growth from the seed during the annealing process. The crystalline region with well-defined tetrahedral local structures is easily observed and is estimated to be 8 at.% by dividing the number of atoms in the crystallite by the total number of atoms. The radial distribution functions of the above-mentioned structures are plotted against the experimental data from neutron scattering in Fig. 5 (c) and show good agreement. A larger crystal seed with 3 at.% was also used to create a paracrystalline silicon structure with the same procedure above, but additional distinctive peaks were clearly seen in the RDF, suggesting that the structural heterogeneity is large enough to affect the sample average of atomic density fluctuations.



FIG. 6. Dispersion relations for longitudinal waves for (a) continuous random network, (b) meltquench, and (c) crystal seed nucleation amorphous silicon structures. All of them show a crisp phonon dispersion line up to around 10 THz above which a significant broadening is observed.

The dispersion relations for longitudinal waves from dynamic structure factor calculations of these 3 amorphous silicon structures are depicted in Fig. 6. We observe that all structures exhibit crisp phonon disperion line up to around 10 THz above which significant broadening is clearly observed, consistent with our IXS measurements. Comparisons of the RDFs and dynamic structure factor calculations between the PECVD a-Si and three amorphous silicon models suggest that acoustic excitations with frequencies up to 10 THz with atomic scale wavelengths exist in several possible atomic configurations of a-Si.

B. IXS measurement comparison among several amorphous materials

The broadening of the inelastic peaks, $\Gamma(q)$, of a-Si at 300 K versus wave vector are shown in Fig. 7 (a) along with those of various types of amorphous materials from metallic glasses to polymers studied by IXS^{18,21,27,30} and the computational work of Ref.⁴². A $\Gamma(q) \alpha q^2$ scaling is also shown as a guide to the eye. Previous works in other materials show a clear power law dependence. In contrast, the broadening of a-Si for both the IXS and dynamic structure factor calculations^{41,42} demonstrate a sudden increase rather than a power law dependence. This sudden increase in the broadening can also be visually observed in the raw data shown in Fig. 2. The origin of this increase is at present not clear and will be the subject of future work.



FIG. 7. Inelastic peak broadening for a-Si (A1 and A2) and other amorphous materials. (a) Broadening Γ versus wave vector q of various amorphous materials from IXS: present measurements at 300 K (black filled triangles for A1 and black filled circles for A2), simulations from Ref.⁴² (solid black line), silica at 1050 K (blue crosses)²⁷, polybutadiene at 140 K (PB, orange squares)¹⁸, Ni₃₃Zr₆₇ metallic glass at room temperature (MG, yellow diamonds)²¹, and amorphous drugs of Indomethacin (IMC, purple circles) and Celecoxib (CXB, green crosses) at room temperature³⁰. A temperature dependence of the broadenings were not observed in these materials; therefore, direct comparison of our measurements at 300 K is possible. The q^2 dependence of broadening on wave vector for these materials is not observed in amorphous silicon. (b) Broadening versus frequency for the same materials as in (a). The dotted line is the Ioffe-Regel crossover defined by $\Omega = \pi\Gamma$. The Ioffe-Regel crossover occurs at around ~ 10 THz for a-Si, well into the thermal frequencies. The vertical bars in the measured data are the uncertainties of fitting the damped harmonic oscillator model to the measurements. The simulated broadening lies within the vertical bars.

The definition of the frequency at which an acoustic excitation is no longer well-defined

is conventionally taken to be when the broadening $\Gamma(q) = \Omega(q)/\pi$, known as the Ioffe-Regel crossover^{2,56}. Using this criterion, we find a strikingly high crossover frequency of around 10 THz, as shown in Fig. 7 (b). This crossover frequency (corresponding to $\hbar\omega/k_B = 480$ K) is well within the portion of the vibrational spectrum thermally occupied at 295 K and implies that acoustic excitations are supported for wavelengths as small as ~ 6 Å, only a few times larger than the interatomic distance of amorphous silicon (~ 2.4 Å).

Our simulations show that this unusually high crossover frequency can be explained by two features of a-Si. First, acoustic excitations cease to possess a well-defined wave vector and frequency if the disorder is sufficiently strong. a-Si is monatomic with only minor isotopic mass disorder and hence lacks the degree of disorder present in polyatomic glasses such as mass or force constant disorder. Using Tersoff potentials^{34,57}, dynamic structure factors of a-SiO₂ and a-SiC were calculated. The longitudinal sound velocities of a-SiO₂ and a-SiC from dynamic structure factors are calculated to be 5567 and 9844 m s⁻¹ which are within 5% of the experimental results of 5800 and 9462 m s⁻¹, respectively^{27,58}. Clear additional broadening in the dispersions is observed compared to a-Si as shown in Fig. 8.



FIG. 8. Calculated dynamic structure factor for longitudinal vibrations in (a) a-SiO₂ and (b) a-SiC. Noticeable broadening is observed for frequencies below 10 THz. The Ioffe-Regel crossover frequency is ~ 1.5 THz and ~ 8 THz for (a) and (b), respectively.

Second, a-Si has a high group velocity due to the low atomic mass of Si and stiff covalent bonds. Thus for a given wave vector a-Si supports higher frequency excitations than for a heavier and weaker bonded amorphous material like glassy selenium. Inelastic neutron and x-ray scattering studies on glassy selenium reported a longitudinal sound velocity of around 2000 m s⁻¹ leading to a Ioffe-Regel crossover frequency of around 1-2 THz^{20,59}. For a given wave vector, a-Si supports a vibrational frequency around four times larger than that of a-Se owing to its higher group velocity. These factors explain the presence of acoustic excitations at frequencies up to 10 THz in a-Si. Other glasses with similar characteristics, such as tetrahedral amorphous carbon, may exhibit such excitations as well, a prediction that can be verified with further inelastic scattering experiments.

V. CONCLUSION

In summary, we report the observation of thermal acoustic excitations with atomic-scale wavelengths in a-Si despite the atomic disorder. The excitations possess wavelengths as small as 6 Å and are supported due to the monatomic composition and high group velocity of a-Si. Our findings demonstrate that the description of thermal vibrations in a-Si as a gas of acoustic excitations is unexpectedly accurate despite the lack of crystalline order, suggesting that other monoatomic glasses with high sound velocity may also support acoustic waves in the thermal spectrum.

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